

#### **Features**

- Trench Power LV MOSFET Technology
- · Excellent Package for Heat Dissipation
- High Density Cell Design for Low R<sub>DS(ON)</sub>
- · Halogen Free. "Green" Device (Note 1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)
- · Moisture Sensitivity Level 1

## **Maximum Ratings**

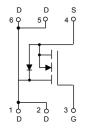
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 43°C/W Junction to Ambient<sup>(2)</sup>

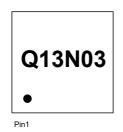
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V <sub>DS</sub>	30	V
Gate-Source Volltage	V <sub>GS</sub>	±20	V
Continuous Drain Current	I <sub>D</sub>	13	Α
Pulsed Drain Current <sup>(3)</sup>	I <sub>DM</sub>	55	Α
Total Power Dissipation	P <sub>D</sub>	2.9	W

#### Note:

- 1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 2.  $R_{\theta JA}$  is the sum of the junction-to-Case and Case-to-ambient thermal resistance, where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design, while  $R_{\theta JA}$  is determined by the board design. The maximum rating presented here is based on mounting on a 1 in  $^2$  pad of 2oz copper.
- 3. Pulse Test: Pulse Width≤300us, Duty cycle ≤2%.

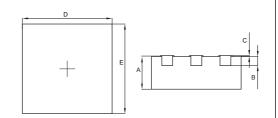
## **Internal Structure and Marking Code**

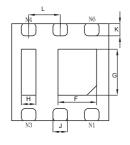




# N-CHANNEL MOSFET

## DFN2020-6LE





DIMENSIONS					
DIM INCHES		MM		NOTE	
Dilvi	MIN	MAX	MIN	MAX	NOIL
Α	0.030	0.033	0.750	0.850	
В	0.008		0.200		REF.
С	0.000	0.002	0.000	0.050	
D	0.075	0.083	1.900	2.100	
E	0.075	0.083	1.900	2.100	
F	0.024	0.031	0.610	0.810	
G	0.028	0.036	0.710	0.910	
Н	0.008	0.016	0.200	0.400	
J	0.010	0.014	0.250	0.350	
K	0.008	0.012	0.200	0.300	
L	0.026		0.650		TYP.

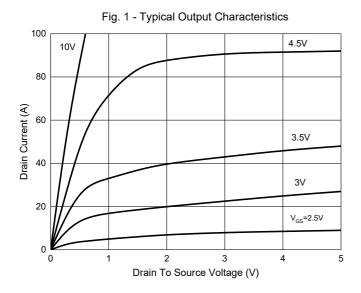


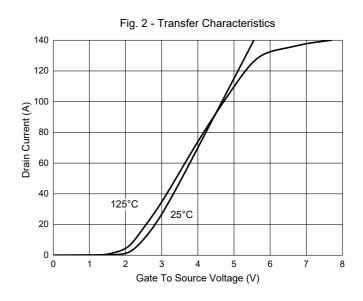
# Electrical Characteristics @ 25°C (Unless Otherwise Specified)

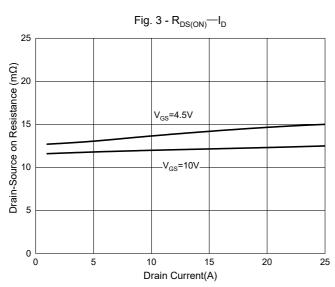
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static Characteristics			'				
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	30			V	
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			±100	nA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V			1	μA	
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , $I_{D}=250\mu A$	1	1.5	2.5	V	
Drain-Source On-Resistance	Б	V <sub>GS</sub> =10V, I <sub>D</sub> =8A		7	12	mΩ	
	R <sub>DS(on)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =5A		11	15	mΩ	
Diode Characteristics					•		
Continuous Body Diode Current	Is				13	Α	
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =13A			1.2	V	
Reverse Recovery Time	t <sub>rr</sub>	1 454 11 / 11 4004 /		5		ns	
Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>F</sub> =15A, dI <sub>F</sub> /dt=100A/μs		0.2		nC	
Dynamic Characteristics					•		
Input Capacitance	C <sub>iss</sub>			1015			
Output Capacitance	C <sub>oss</sub>	$V_{DS}$ =15V, $V_{GS}$ =0V,f=1MHz		201		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			164			
Total Gate Charge	Qg			23.6			
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =10V,V <sub>GS</sub> =10V,I <sub>D</sub> =20A		3.8		nC	
Gate-Drain Charge	$Q_{gd}$			7			
Turn-On Delay Time	t <sub>d(on)</sub>			7			
Turn-On Rise Time	t <sub>r</sub>	V <sub>DS</sub> =20V, V <sub>GS</sub> =10V,		20		no	
Turn-Off Delay Time	t <sub>d(off)</sub>	$R_G=3\Omega$ , $I_{DS}=2A$		24		ns	
Turn-Off Fall Time	t <sub>f</sub>			24			

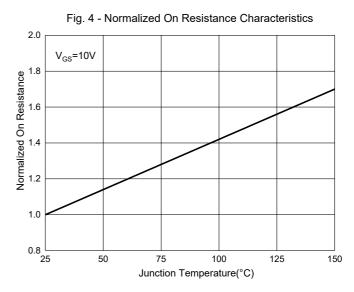


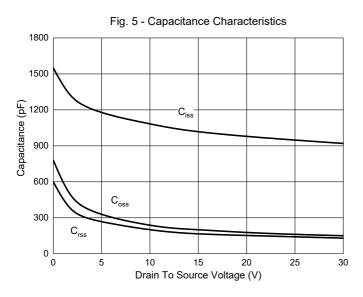
#### **Curve Characteristics**

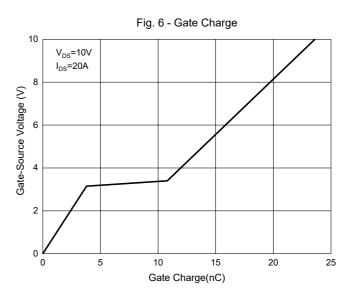














#### **Curve Characteristics**

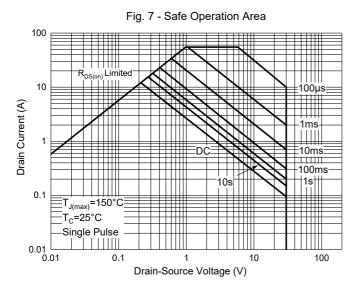
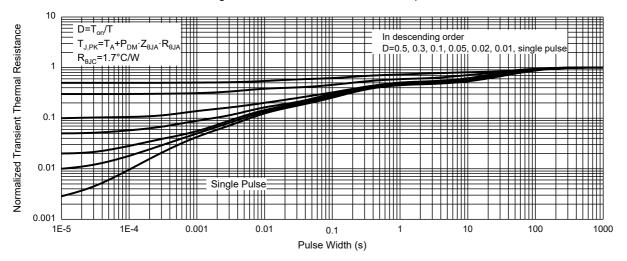


Fig. 8 - Normalized Transient Thermal Impedance





## **Ordering Information**

Device	Packing	
Part Number-TP	Tape&Reel: 3Kpcs/Reel	

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